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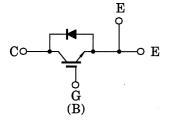
TOSHIBA GTR Module Silicon N Channel IGBT

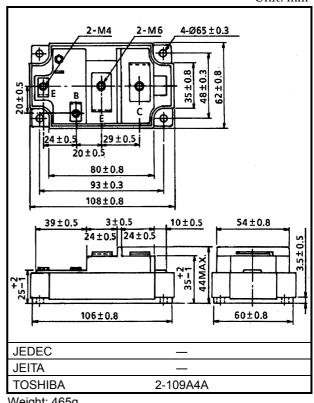
# **MG500Q1US1**

**High Power Switching Applications** Motor Control Applications

- High input impedance
- High speed :  $t_f = 0.5 \mu s$  (Max)  $t_{rr} = 0.5 \mu s$  (Max)
- Low saturation voltage •
  - : VCE (sat) = 4.0V (Max)
- Enhancement-mode
- The electrodes are isolated from case

### **Equivalent Circuit**





Weight: 465g

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ι <sub>C</sub>	500	A	
	1ms	I <sub>CP</sub>	1000		
Forward current	DC	١ <sub>F</sub>	500	A	
	1ms	I <sub>FM</sub>	1000		
Collector power dissipation (Tc = 25°C)		PC	2400	W	
Junction temperature		Тј	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−</b> 40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC, 1 min)	V	
Screw torque (Terminal : M4 / M6 / mounting)		—	2/3/3	N∙m	

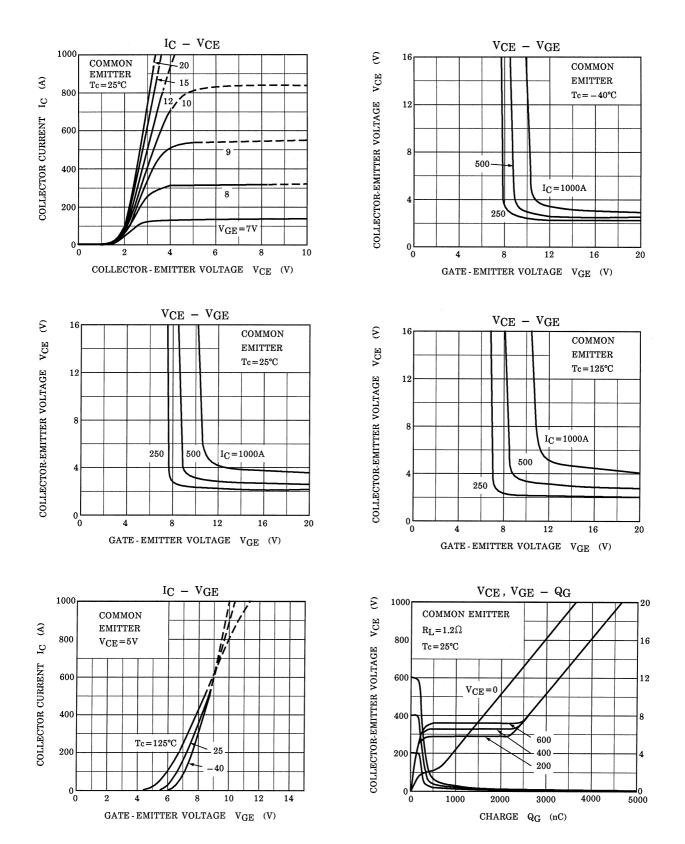
### Maximum Ratings (Ta = 25°C)

Unit: mm

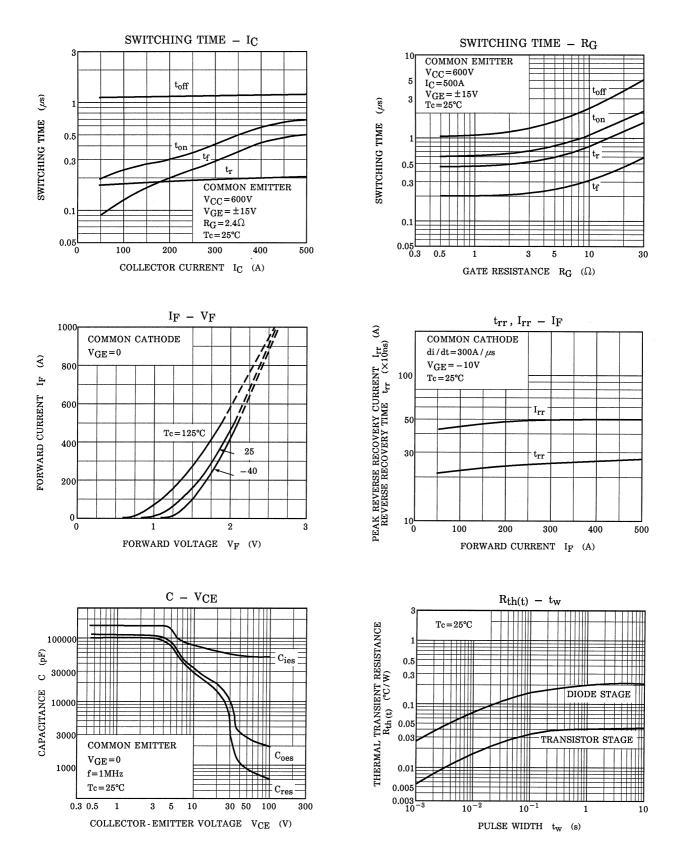
Electrical Characteristics (Ta = 25°C)

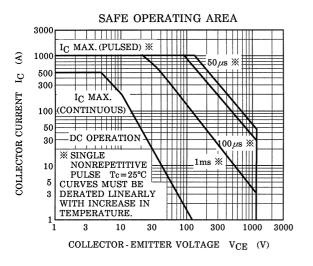
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		IGES	$V_{GE} = \pm 20V, V_{CE} = 0$	_	_	±500	nA
Collector cut-off current I <sub>CES</sub> V <sub>CE</sub> = 1200 V <sub>GE</sub> =		V <sub>CE</sub> = 1200 V <sub>GE</sub> = 0	_	_	4.0	mA	
Gate-emitter cut-off voltage V <sub>GE (OFF)</sub>		V <sub>GE (OFF)</sub>	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 5V	3.0	_	6.0	V
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	) I <sub>C</sub> = 500A, V <sub>GE</sub> = 15V		3.0	4.0	V
Input capacitance	9	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz		80000	_	pF
Switching time Fall	Rise time	tr	$15V_{0}$	_	0.3	0.6	μs
	Turn-on time	t <sub>on</sub>		_	0.4	0.8	
	Fall time	t <sub>f</sub>		_	0.2	0.5	
	Turn-off time	t <sub>off</sub>		_	0.8	1.5	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 500 A, V <sub>GE</sub> = 0	_	_	3.0	V
Reverse recovery time tr		t <sub>rr</sub>	I <sub>F</sub> = 500 A, V <sub>GE</sub> = −10 V, di / dt = 300 A / μs	_	0.25	0.5	μs
Thermal resistance		R <sub>th (j-c)</sub>	Transistor	_	_	0.042	°C/W
			Diode	_	_	0.20	

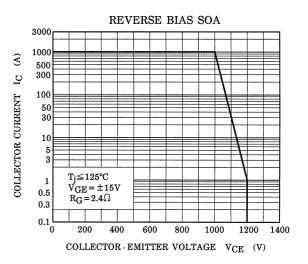
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